

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1-2. (canceled)

3. (original) A display device comprising:

a first substrate having a pixel matrix region;

a switching thin film transistor provided over the first substrate in the pixel matrix region;

a pixel electrode connected to the switching thin film transistor and provided over the first substrate in the pixel matrix region;

a second substrate comprising an insulator provided over the first substrate outside the pixel matrix region;

a drive circuit for driving the pixel matrix region, the drive circuit provided over the second substrate;

a plurality of first lead wirings provided outside the pixel matrix region over the second substrate and connected to the drive circuit;

a plurality of second lead wirings provided over the first substrate and extending from the pixel matrix region toward the second substrate;

first electrode pads arranged at end portions of the plurality of first lead wirings;

second electrode pads having an area smaller than that of the first electrode pads and arranged at end portions of the plurality of second lead wirings; and

a conductive member provided over the first substrate and connecting at least one of the first electrode pads with corresponding one of the second electrode pads,

wherein contiguous ones of the first electrode pads with each other are shifted in a direction of a side of the second substrate.

4. (original) A display device comprising:

- a first substrate having a pixel matrix region;
- a switching thin film transistor provided over the first substrate in the pixel matrix region;
- a pixel electrode connected to the switching thin film transistor and provided over the first substrate in the pixel matrix region;
- a second substrate comprising an insulator provided over the first substrate outside the pixel matrix region;
- a drive circuit for driving the pixel matrix region, the drive circuit provided over the second substrate;
- a plurality of first lead wirings provided outside the pixel matrix region over the second substrate and connected to the drive circuit;
- a plurality of second lead wirings provided over the first substrate and extending from the pixel matrix region toward the second substrate;
- first electrode pads arranged at end portions of the plurality of first lead wirings;
- second electrode pads having an area smaller than that of the first electrode pads and arranged at end portions of the plurality of second lead wirings; and
- a conductive member provided over the first substrate and connecting at least one of the first electrode pads with corresponding one of the second electrode pads,

wherein contiguous ones of the first electrode pads with each other are shifted periodically in a direction of a side of the second substrate.

5-23. (canceled)

24. (original) A device according to claim 3 wherein the pixel matrix region comprises a reverse staggered thin film transistor.

25. (original) A device according to claim 3 wherein the first substrate comprises a glass.

26. (original) A device according to claim 23 wherein the second substrate comprises a quartz.

27. (original) A device according to claim 3 wherein the pixel matrix region comprises a thin film transistor having a channel etch type structure.

28. (original) A device according to claim 3 wherein the drive circuit comprises a thin film transistor comprising an activation layer having a thickness of 20 to 100 nm and comprising silicon.

29. (original) A device according to claim 3 wherein the first substrate and the second substrate have a same thickness.

30. (original) A device according to claim 29 wherein the first substrate and the second substrate have a thickness of 1mm.

31. (original) A device according to claim 3 wherein the drive circuit comprises a thin film transistor having an activation layer comprising a material selected from the group consisting of a polycrystalline silicon, a microcrystal silicon, an amorphous silicon including a crystal component, and a semiamorphous silicon having a state of an intermediary between the crystalline performance and the amorphous performance.

32. (original) A device according to claim 3 wherein the conductive member comprises a bump, an anisotropic conductive film, conductive small particles, or an FPC.

33. (original) A device according to claim 4 wherein the pixel matrix region comprises a reverse staggered thin film transistor.

34. (original) A device according to claim 4 wherein the first substrate comprises a glass.

35. (original) A device according to claim 4 wherein the second substrate comprises a quartz.

36. (original) A device according to claim 4 wherein the pixel matrix region comprises a thin film transistor having a channel etch type structure.

37. (original) A device according to claim 4 wherein the drive circuit comprises a thin film transistor comprising an activation layer having a thickness of 20 to 100 nm and comprising silicon.

38. (original) A device according to claim 4 wherein the first substrate and the second substrate have a same thickness.

39. (original) A device according to claim 38 wherein the first substrate and the second substrate have a thickness of 1mm.

40. (original) A device according to claim 4 wherein the drive circuit comprises a thin film transistor having an activation layer comprising a material selected from the group consisting of a polycrystalline silicon, a microcrystal silicon, an amorphous silicon including a crystal component, and a semiamorphous silicon having a state of an intermediary between the crystalline performance and the amorphous performance.

41. (original) A device according to claim 4 wherein the conductive member comprises a bump, an anisotropic conductive film, conductive small particles, or an FPC.

42-52. (canceled)

53. (original) A device according to claim 3 wherein the second substrate has a strain point of 750°C or higher.

54. (original) A device according to claim 4 wherein the second substrate has a strain point of 750°C or higher.

55. (canceled)

56. (new) A semiconductor device comprising:

a transistor provided over a first substrate in a pixel matrix, said pixel matrix provided with a plurality of first lead wirings;

a pixel electrode connected to said transistor and provided over said first substrate in said pixel matrix;

a drive circuit for driving said pixel matrix; and

a plurality of second lead wirings connected to said drive circuit;

wherein each of said first lead wirings is connected to corresponding one of said second lead wirings through corresponding one of electrode pads,

wherein a width of at least one of said electrode pads is larger than line interval between contiguous ones of said first lead wirings with each other, and

wherein contiguous ones of said electrode pads with each other are shifted in a direction perpendicular to a direction of said width of at least one of said electrode pads.

57. (new) A device according to claim 56 further comprising a conductive member wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said conductive member.

58. (new) A device according to claim 56 further comprising a bump wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said bump.

59. (new) A device according to claim 56 further comprising an anisotropic conductive film wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said anisotropic conductive film.

60. (new) A device according to claim 56 further comprising conductive small particles wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said conductive small particles.

61. (new) A device according to claim 56 wherein said first substrate comprises a glass.

62. (new) A semiconductor device comprising:

- a transistor provided over a first substrate in a pixel matrix, said pixel matrix provided with a plurality of first lead wirings;

- a pixel electrode connected to said transistor and provided over said first substrate in said pixel matrix;

- a drive circuit for driving said pixel matrix; and

- a plurality of second lead wirings connected to said drive circuit;

wherein each of said first lead wirings is connected to corresponding one of said second lead wirings through corresponding one of electrode pads,

wherein a width of at least one of said electrode pads is larger than line interval between contiguous ones of said first lead wirings with each other, and

wherein said electrode pads are staggered.

63. (new) A device according to claim 62 further comprising a conductive member wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said conductive member.

64. (new) A device according to claim 62 further comprising a bump wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said bump.

65. (new) A device according to claim 62 further comprising an anisotropic conductive film wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said anisotropic conductive film.

66. (new) A device according to claim 62 further comprising conductive small particles wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said conductive small particles.

67. (new) A device according to claim 62 wherein said first substrate comprises a glass.

68. (new) A semiconductor device comprising:

- a transistor provided over a first substrate in a pixel matrix, said pixel matrix provided with a plurality of first lead wirings;

- a pixel electrode connected to said transistor and provided over said first substrate in said pixel matrix;

- a drive circuit for driving said pixel matrix; and

- a plurality of second lead wirings connected to said drive circuit;

wherein each of said first lead wirings is connected to corresponding one of said second lead wirings through corresponding one of electrode pads,

wherein a width of at least one of said electrode pads is larger than line interval between contiguous ones of said first lead wirings with each other,

wherein said electrode pads are staggered, and

wherein said transistor comprises:

a source region and a drain region;

a channel region provided between said source region and said drain region; and

a gate electrode provided adjacent to said channel region with a gate insulating film therebetween.

69. (new) A device according to claim 68 further comprising a conductive member wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said conductive member.

70. (new) A device according to claim 68 further comprising a bump wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said bump.

71. (new) A device according to claim 68 further comprising an anisotropic conductive film wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said anisotropic conductive film.

72. (new) A device according to claim 68 further comprising conductive small particles wherein corresponding one of said first lead wirings is connected to corresponding one of said second lead wirings through said conductive small particles.

73. (new) A device according to claim 68 wherein said first substrate comprises a glass.